

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

The ASI HF10-12F is Designed for

**FEATURES:**

- $P_G = 20$  dB min. at 10 W/30 MHz
- $IMD_3 = -30$  dBc max. at 10 W (PEP)
- *Omnigold*<sup>TM</sup> Metalization System

**MAXIMUM RATINGS**

$I_C$	4.5 A
$V_{CBO}$	36 V
$V_{CEO}$	18 V
$V_{EBO}$	4.0 V
$P_{DISS}$	80 W @ $T_C = 25^\circ C$
$T_J$	$-65^\circ C$ to $+200^\circ C$
$T_{STG}$	$-65^\circ C$ to $+150^\circ C$
$q_{JC}$	$2.2^\circ C/W$

**PACKAGE STYLE .380 4L FLG**

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.785 / 19.94	
C	.720 / 18.29	.730 / 18.54
D	.970 / 24.64	.980 / 24.89
E		.385 / 9.78
F	.004 / 0.10	.006 / 0.15
G	.085 / 2.16	.105 / 2.67
H	.160 / 4.06	.180 / 4.57
I		.280 / 7.11
J	.240 / 6.10	.255 / 6.48

**ORDER CODE: ASI10592**

**CHARACTERISTICS**  $T_C = 25^\circ C$ 

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CBO}$	$I_C = 50$ mA	36			V
$BV_{CES}$	$I_C = 50$ mA	36			V
$BV_{CEO}$	$I_C = 50$ mA	18			V
$BV_{EBO}$	$I_E = 5$ mA	4.0			V
$I_{CES}$	$V_{CE} = 15$ V			5	mA
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 1.0$ A	10		200	---
$C_{ob}$	$V_{CB} = 12.5$ V $f = 1.0$ MHz		100		pF
$G_{PE}$	$V_{CC} = 12.5$ V $I_{CQ} = 25$ mA $f = 30$ MHz	15	18	---	dB
$IMD_3$	$P_{OUT} = 10$ W(PEP)			-30	dB